

# Detection of antiproton annihilation with silicon detectors of different geometry

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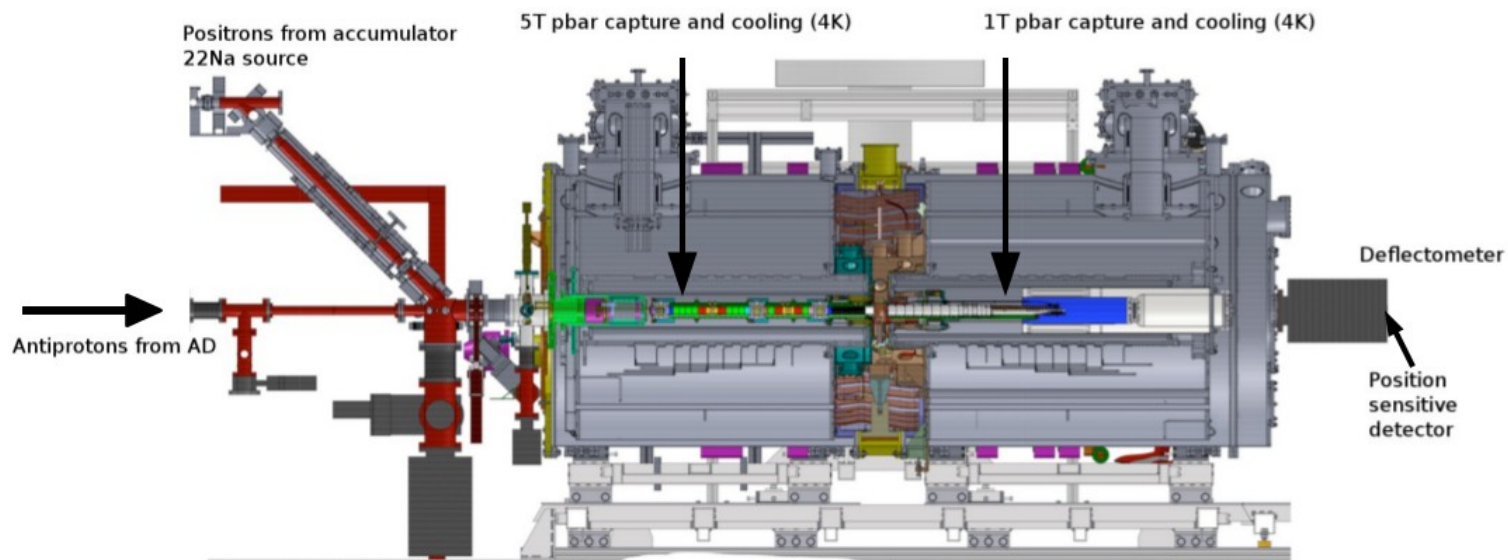
Hiroshima, HSTD 9, 2013



# + Outline

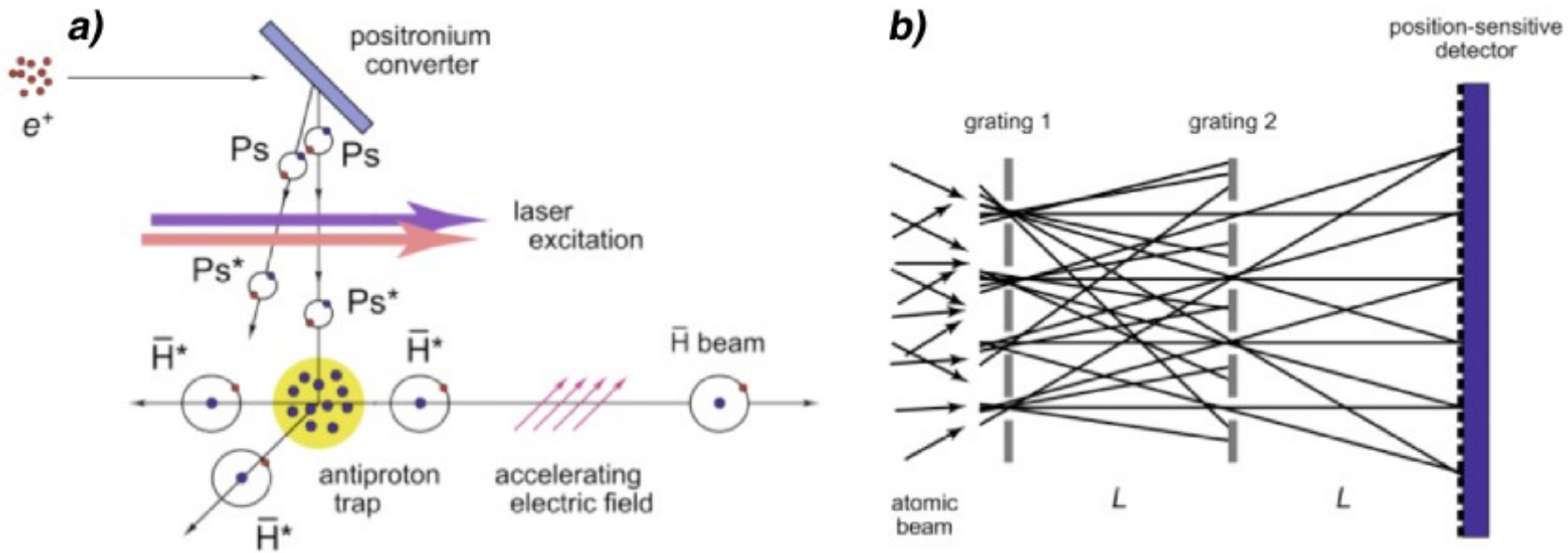
- A silicon antihydrogen detector for the AEGIS experiment
  - The AEGIS experiment
  - Working principle of AEGIS
  - Aim and requirements for the silicon sensor
- Test beams:
  - Previous results: the MIMOTERA detector
  - Miniature strip sensors, Alibava readout
  - CNM 3D detector with FE-I4 readout
- Results
- Conclusions and further developments

# + AEgIS – Section view of the main apparatus.



- Aim of AEgIS is the determination of the gravitational acceleration of antihydrogen in Earth's gravitational field.

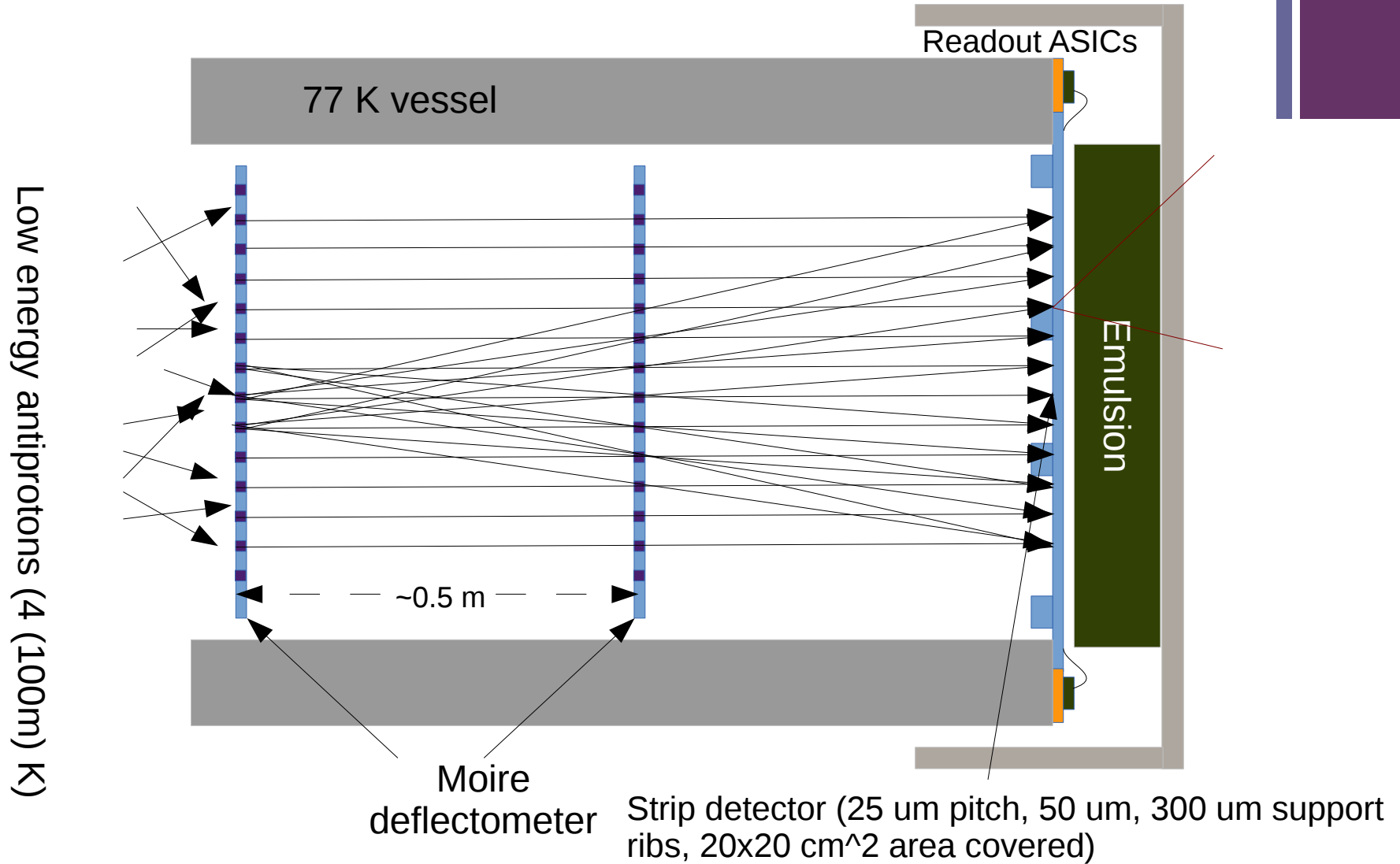
# + Producing and detecting the antihydrogen



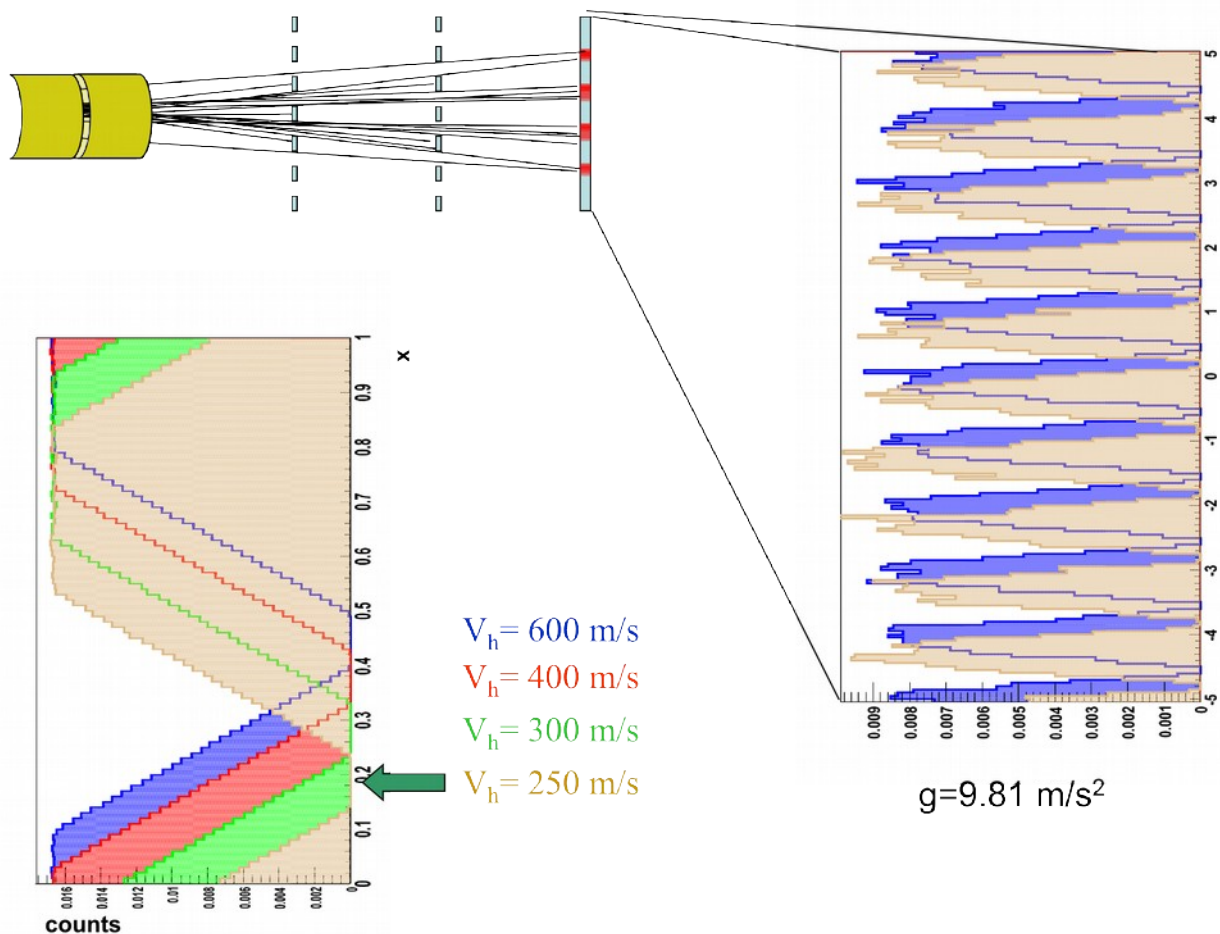
- Thermal motion of antihydrogen (though cold, to 4K and eventually to 100 mK) also has a random transversal component.
- Path selection is made by means of a Moire deflectometer, a TOF measurement is required to know the longitudinal component.



# The Moire deflectometer and the Hybrid detector



# + How we measure $g_{\text{bar}}$ ?



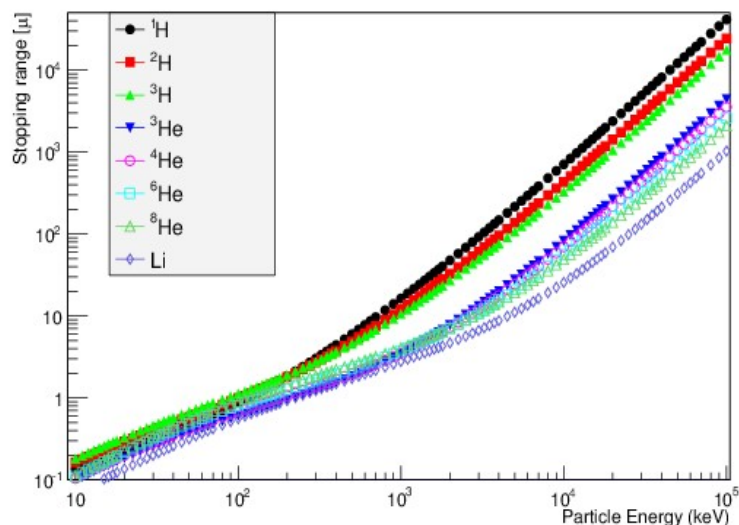
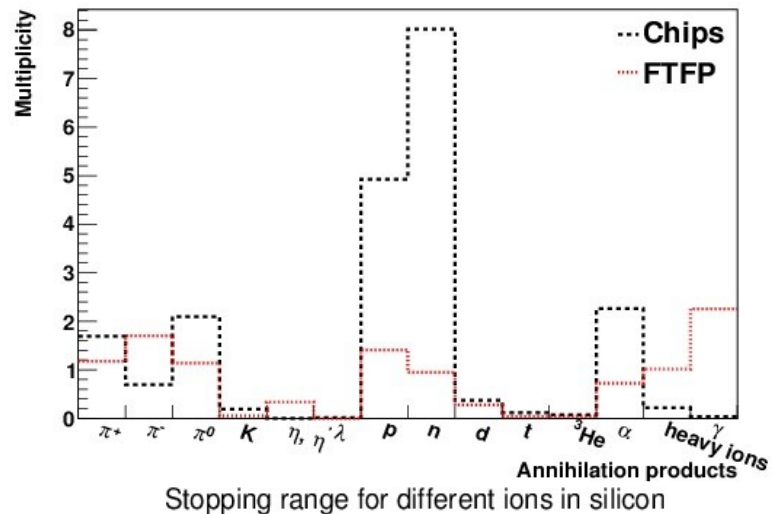
- Shift of the fringes wrt horizontal path proportional to  $g_{\text{bar}}$  on antihydrogen
- High resolution required (better than 5  $\mu\text{m}$  for measuring a 20  $\mu\text{m}$  deflection of the pattern) to achieve 1% precision on  $g_{\text{bar}}$  at expected statistics
- Main source of error from multiple scattering of annihilation products.



# Aims of the AEgIS silicon detector

- Observation of direct annihilation on a silicon strip detector
- Online beam quality check
- High efficiency (90%) in the detection of antihydrogen
- Measurement of the annihilation position of the antihydrogen with a single hit resolution better than 25  $\mu\text{m}$ , providing a search seed for the downstream emulsion detector.
- Precision measurement of the TOF of single antiprotons

# + Annihilations in silicon



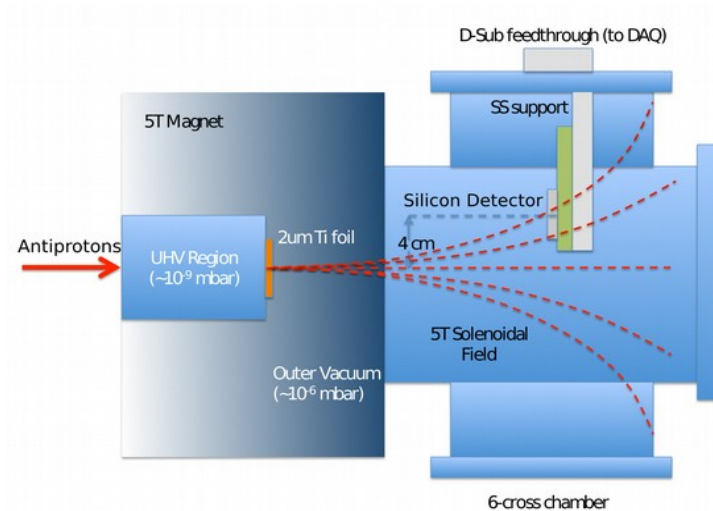
- Annihilation of antiprotons with a nucleon produces mainly pi-mesons
- If the annihilation happens within a nucleus of a heavier element, pions may interact and cause nuclear fragmentation
- Detection of annihilation is made through the detection of charged annihilation products (pi-mesons, protons, heavy nuclear fragments)
- Total kinetic energy of products emitted in annihilations up to  $\sim 1,880$  MeV



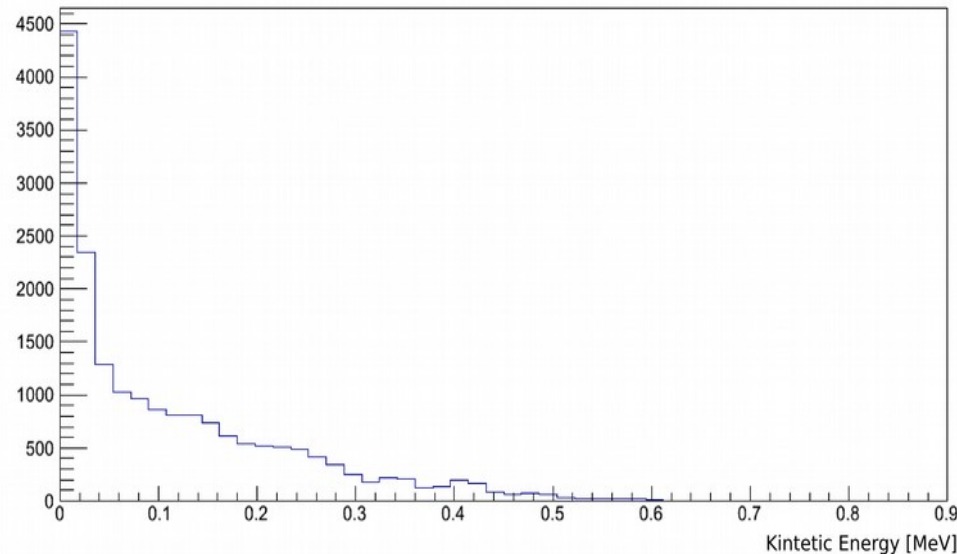
# + Test beam

Aim:  
Understand the signature of annihilation events in silicon in different kinds of silicon sensors.

- Spill composed by  $10^7$  antiprotons
- Spill spacing  $\sim 100$  keV
- Antiproton energy spectrum slowed down to  $\sim 100$  keV by means of Aluminum degraders
- Annihilations expected within  $\sim 15$   $\mu\text{m}$  from detector surface
- Detector mounted in vacuum chamber, vacuum level  $10^{-7}$  mbar
- Tests took place during 5 days in december 2012

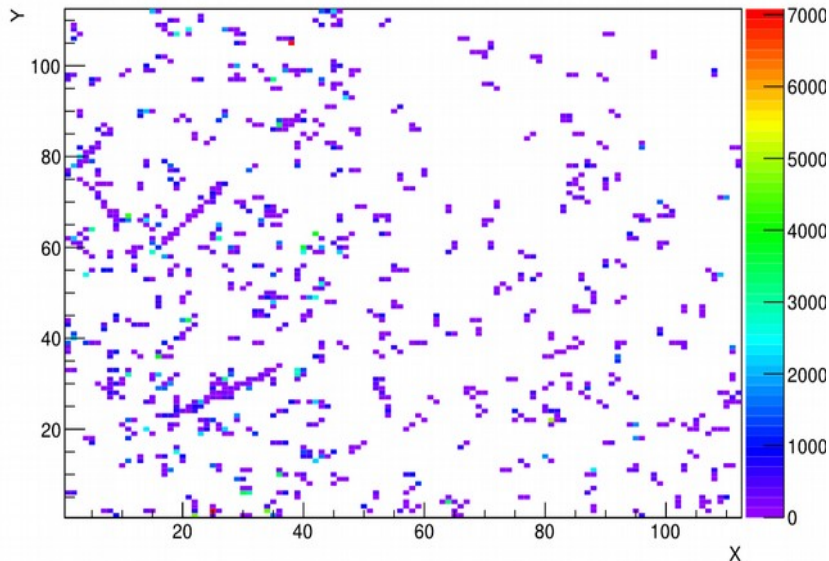
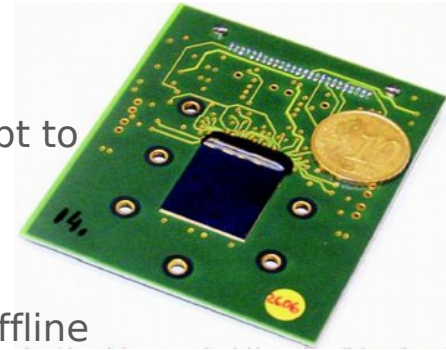


kinetic energy (in) at deg15 (run 1096)

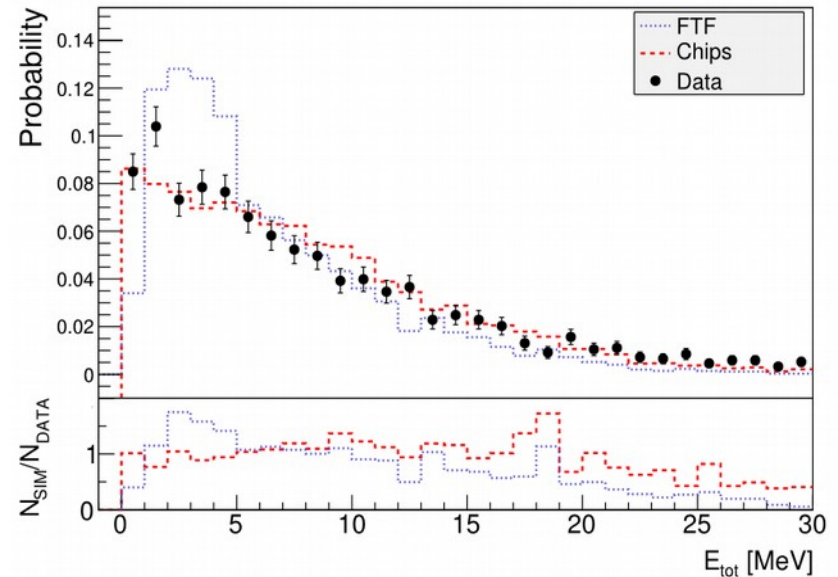


# + Previous results

- Previous test-beam (May, 2012) using the Mimotera (Monolithic diffusion pixel) – First ever (successful) attempt to measure antiproton annihilation directly on silicon!
- 14  $\mu\text{m}$  thickness, pixel size 153x153  $\mu\text{m}$
- 2.5 MHz total analog readout without zero suppression (offline cut of noise events)



Sample frame of an annihilation event after noise and background suppression.



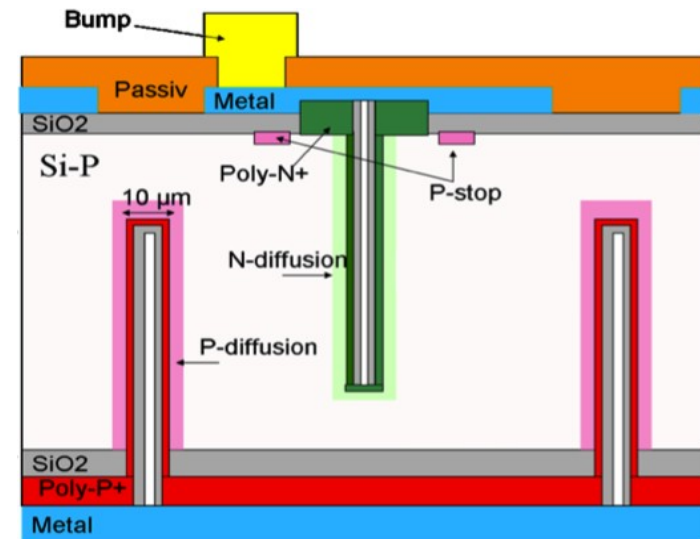
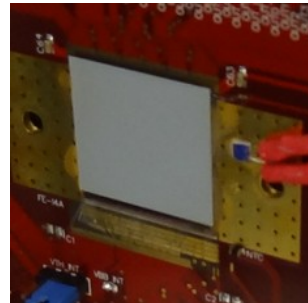
Cluster energy spectrum with Geant4 comparison.

# + Tested sensors

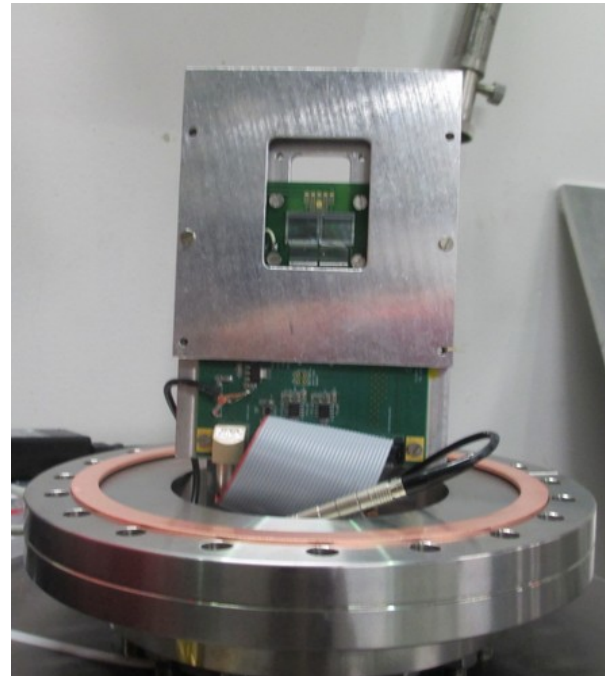
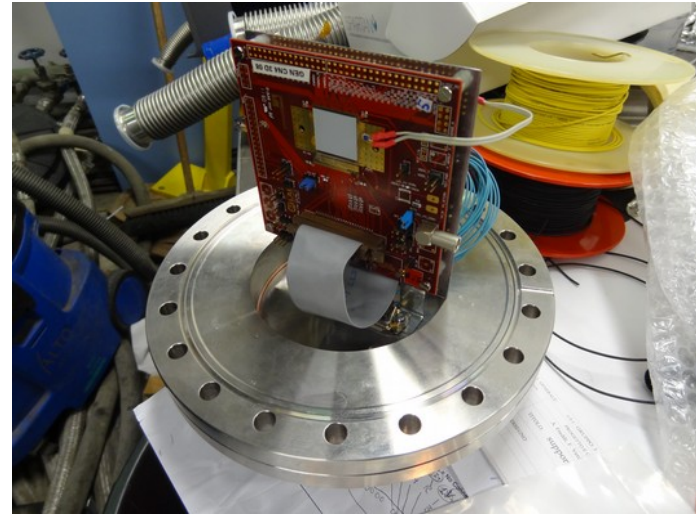
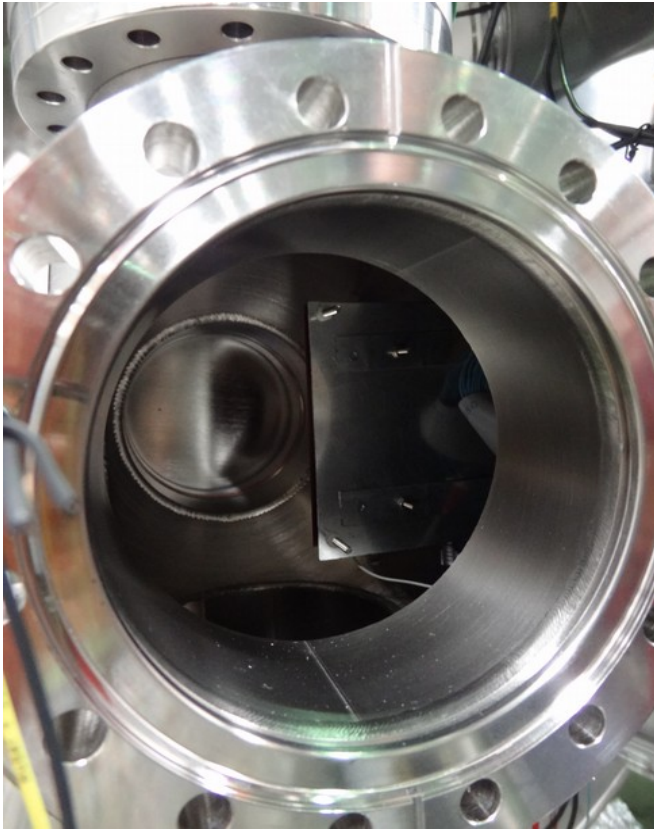


- Two silicon strip sensors:
  - Sensor 1: 300  $\mu\text{m}$  thickness, 80  $\mu\text{m}$  pitch, 128 strips, 1 cm strip length.
  - Sensor 2: 300  $\mu\text{m}$  thickness, 50  $\mu\text{m}$  pitch, 128 consecutive strips connected, 1 cm strip length
- Sensors, realized on MCz silicon, were provided courtesy of HIP.
- Sensors' depletion voltage  $\sim 120$  V.

- CNM 3D sensor, developed for the IBL:
- 230  $\mu\text{m}$  thickness, electrode diameter of 10  $\mu\text{m}$
- Bias voltage down to -30 V
- Pixel dimensions: 50  $\mu\text{m}$  x 250  $\mu\text{m}$ , 80(col) x 336 (rows) = 26880 cells.
- 2cm x 2cm
- 2 $\mu\text{m}$  passive material on surface (stopping slower particles)

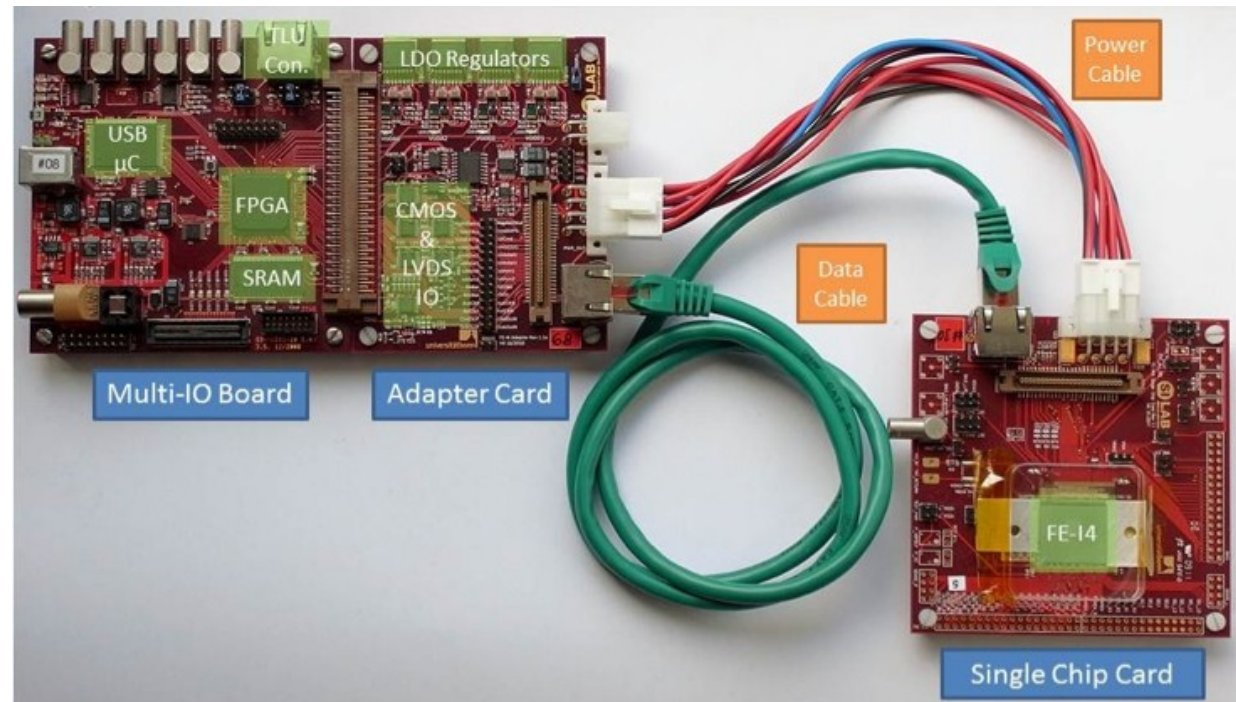
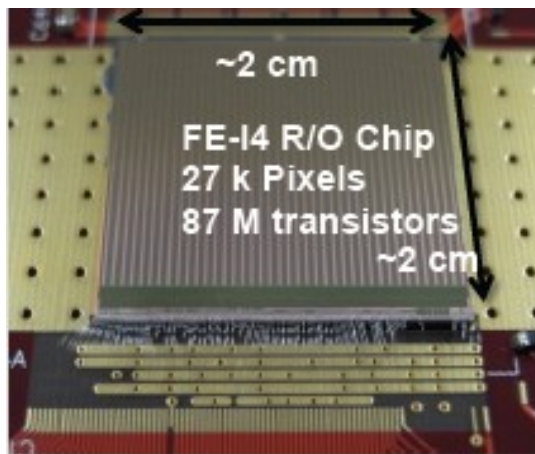


# + Detector mounting and measurements



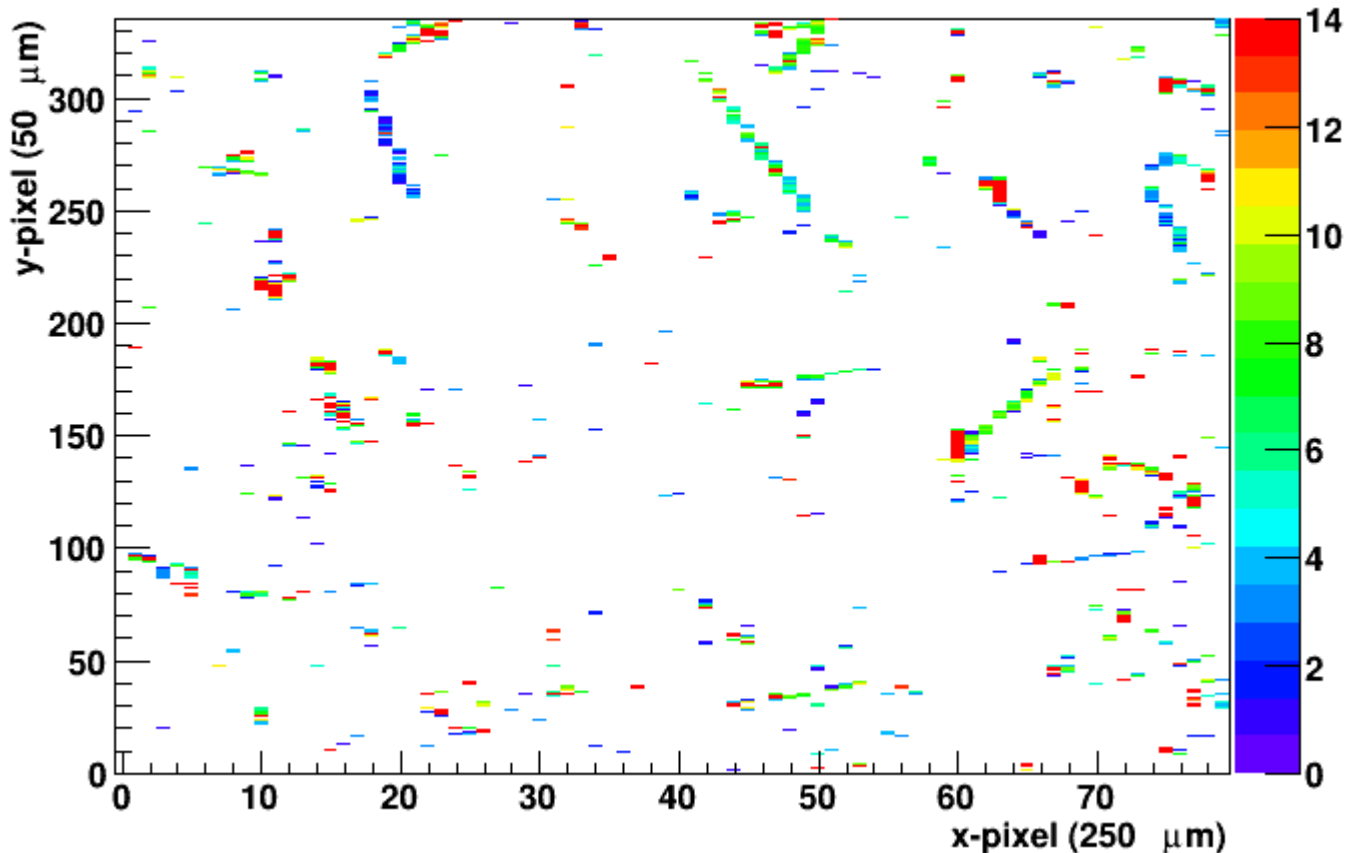
# + 3D detector: readout system

- Multipurpose I/O board with USB interface
- Adapter card
- Single chip card (sensor front end) with FE-I4 readout: (50x250  $\mu\text{m}$  cells)
- Zero-suppressed readout



# + 3D: annihilation event

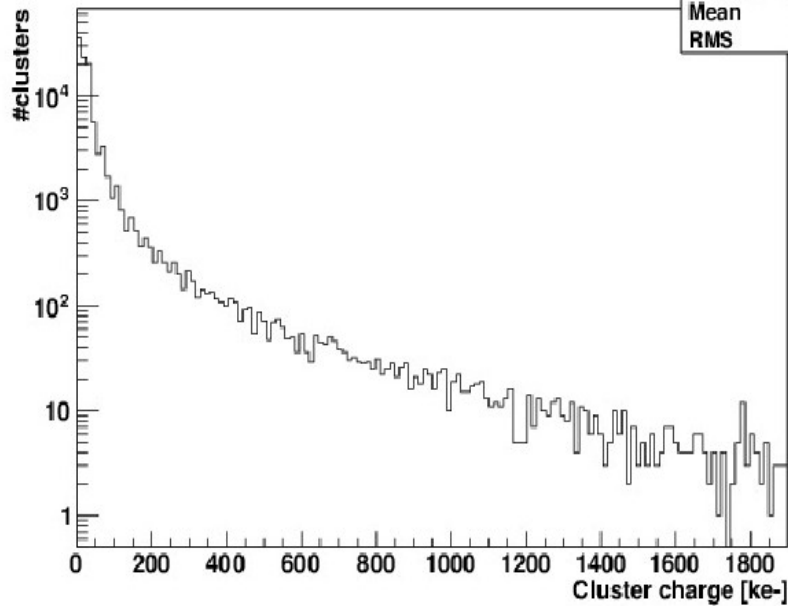
Hitmap single event



- Saturation of a few pixel (high energetic fragment at annihilation point)
- Long tracks recorded with different energy deposits (pions - blue tracks, protons, green to turquoise tracks)

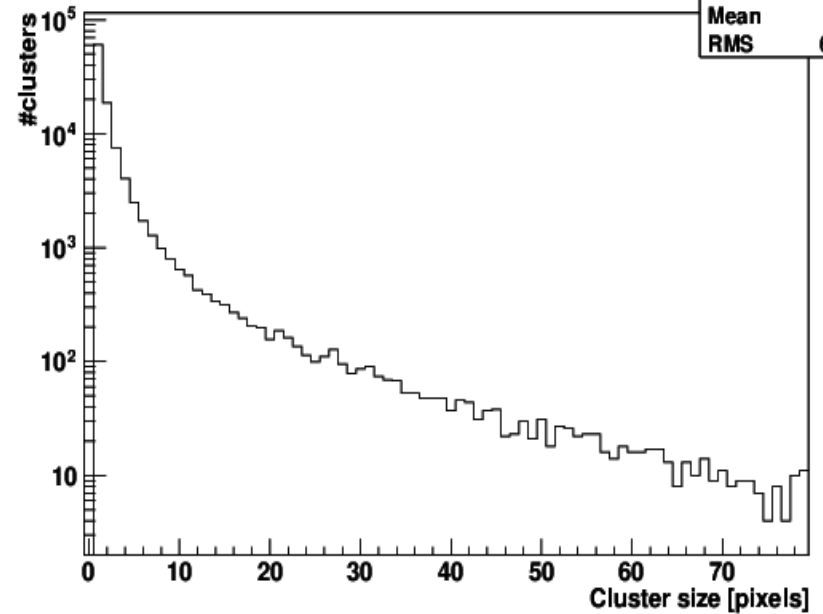
# + 3D cluster analysis

Cluster charge distribution



hClusterCharge	
Entries	104454
Mean	54.58
RMS	136

Cluster size distribution



hClusterSize	
Entries	104454
Mean	3.111
RMS	6.184

- Wide spread of cluster size (long in-plane pion tracks)
- Cluster energy in excess of 10 MeV.

# + Strip detector: readout system



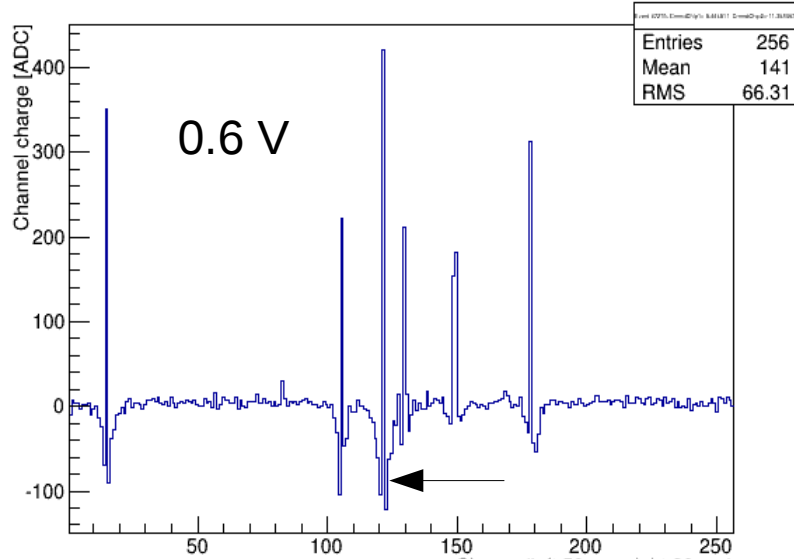
- The tests were performed using the Alibava test system, provided courtesy of RD50 collaboration.
- USB readout making use of two Beetle chips (LHCb Velo) with 25 ns shaping, 128 channels each
- Triggering was done on AegIS silicon beam condition monitor scanning manually through different latencies
- Given Alibava DAQ incompatibility with slow triggers, a 30 Hz trigger was continuously running (pedestals), 'OR'ed with the trigger from the Antiproton Decelerator.



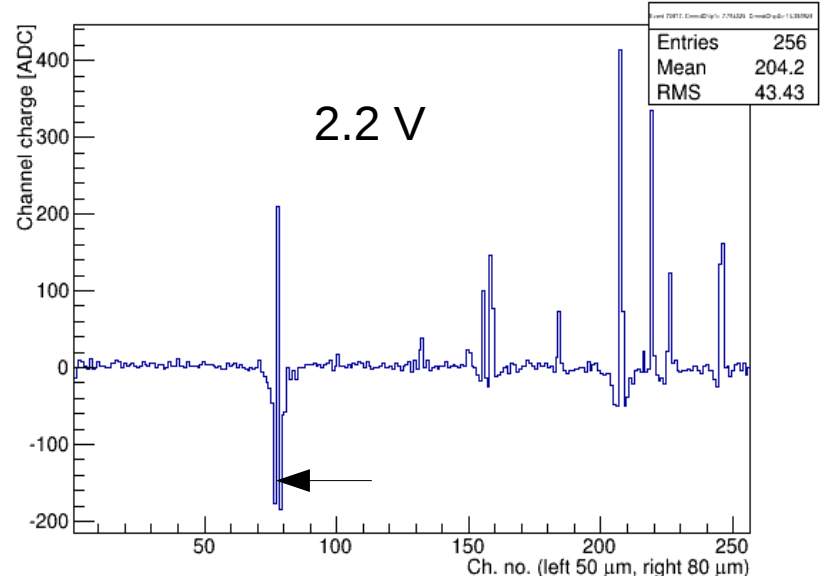


# Sample frames at different Vbias

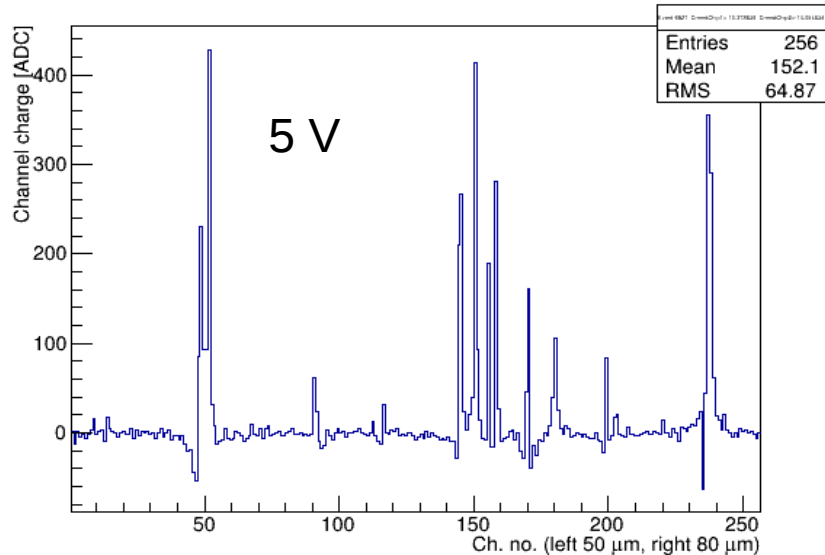
Event-47275, CmmChip1=-8.444811, CmmChip2=-11.358497



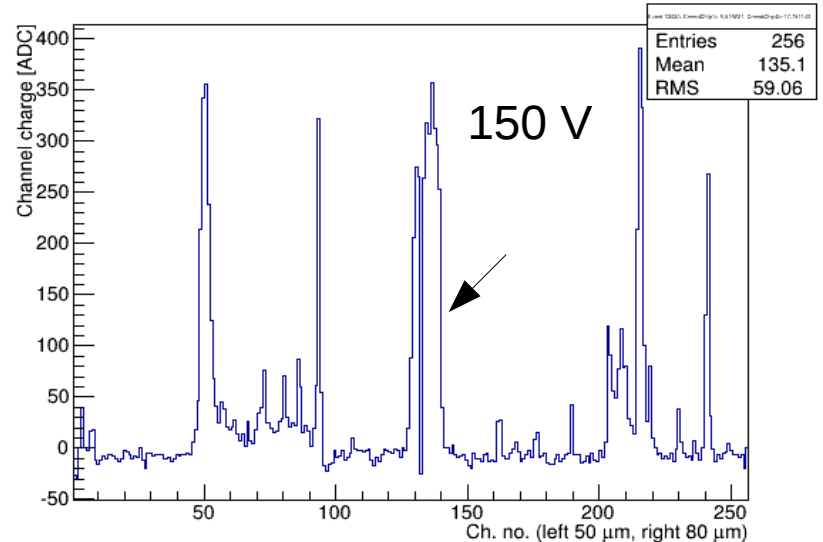
Event-70977, CmmChip1=-7.784025, CmmChip2=-14.396929



Event-6827, CmmChip1=-10.378639, CmmChip2=-14.054834



Event-33020, CmmChip1=-5.519721, CmmChip2=-17.751140

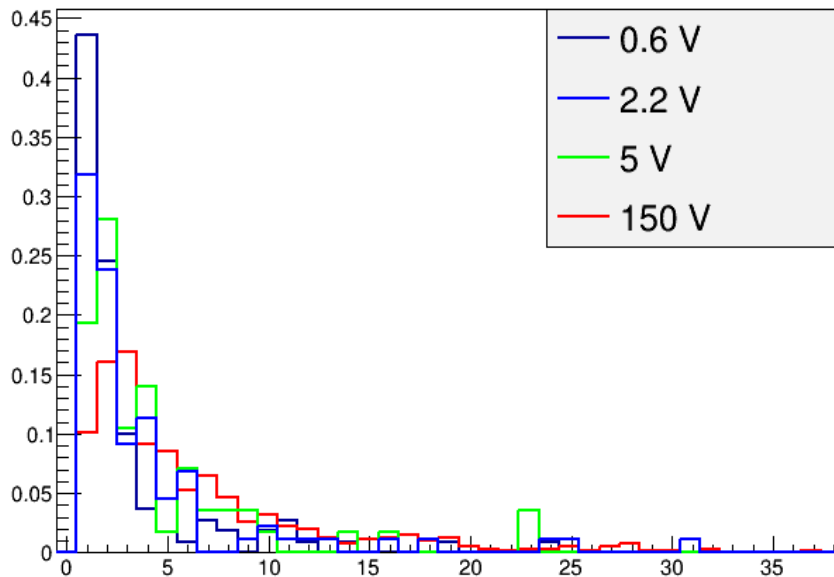


Varying Vbias to “virtually” test different detector thicknesses

# + Strip: cluster analysis

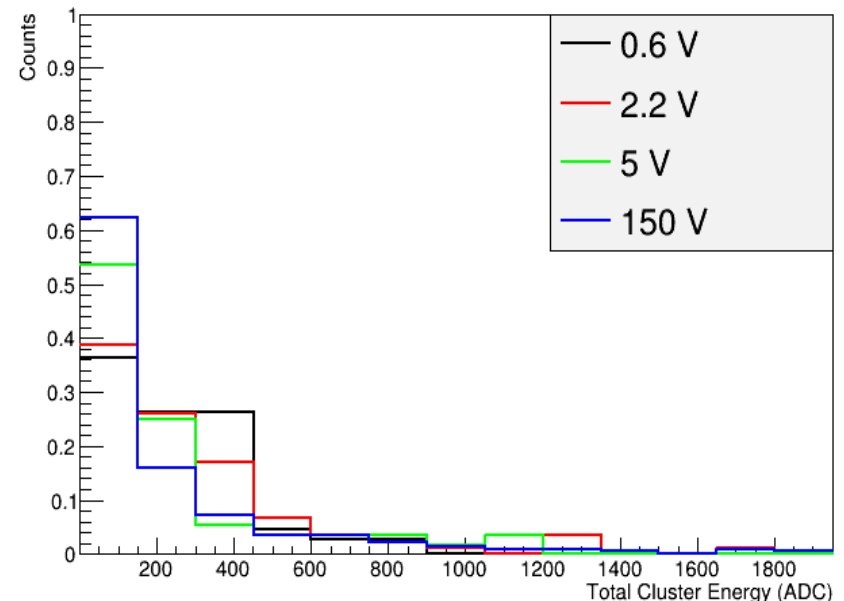
- Selection on the frames with lower occupancy (<40%)
- Clusters defined at > 5 noise RMS conglomerates of strips (no seeding algorithm possible here)

ClusterSize



Decrease in the active volume corresponds to a lower sensitivity to long-travelling (low-ionizing particles): Improved position resolution.

Cluster energy spectrum



Decreased sensitivity to long-travelling products (low ionizing) affects the distribution at lower voltages.

# + Strips: considerations on the active volume / thickness of the detector

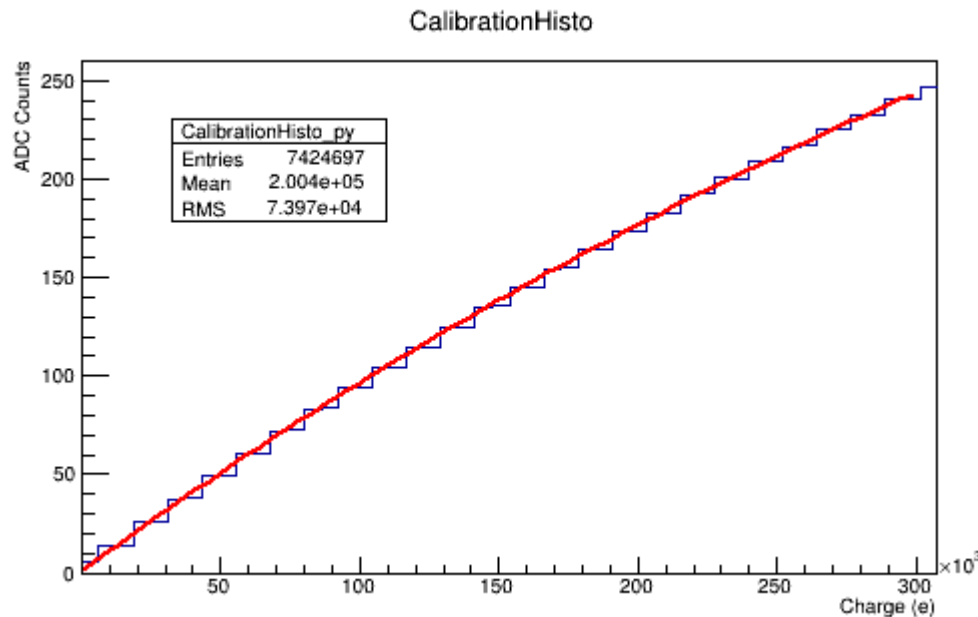
- Events at low applied bias voltage (20 to 50  $\mu\text{m}$  depletion) are very localized (max 2 strips in 70% of the events)
- Low voltage brings to consistent undershoots in the strip neighboring the event: increase in the interstrip capacitance
- Higher voltages (full detector depletion) result in extension of the active volume: annihilation products with long range can extend considerably the cluster (even to millimeters), negatively affecting the detector resolution.

# + Conclusions and developments

- Cluster composition (heterogeneity) doesn't allow the reconstruction of the annihilation position by standard centre of mass methods in the strip detector.
- Primary source of resolution is the position of short-travelling products (heavy fragments) which can be identified by large and localized energy release
- Resolution down to foreseen strip pitch width for the final detector
- Resolution on the fringes should be achieved in the final detector to  $25 \text{ um} / \sqrt{12} \sim 8 \text{ um}$ .
- The requirement of having a thin detector (avoid multiple scattering of products) is compatible with having the highest possible resolution achievable with the sensor technology.

# + Backups

Alibava calibration curve up to 300 ke:



$$ADC = a \cdot [1 - \exp(-b \cdot charge)] \quad A=5.89e2, B=1.77e-6$$